

General Description

The WSD90P06DN56 is the highest performance trench P-ch MOSFETs with extreme high cell density, which provide excellent R_{DS(on)} and gate charge for most of the synchronous buck converter applications.

The WSD90P06DN56 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

Product Summary

BVDSS	R _{DS(on)}	I _D
-60V	10.5mΩ	-90A

Applications

- Power Management
- Load Switch

DFN5X6_8L Pin Configuration



Absolute Maximum Ratings

DFN5*6-8L

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-60	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current, -V _{GS} @ -10V	-90	A
I _D @T _C =100°C	Continuous Drain Current, -V _{GS} @ -10V	-39.7	A
I _{DM}	Pulsed Drain Current	-189	A
P _D @T _C =25°C	Total Power Dissipation	96	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-Ambient	---	23	°C/W
R _{θJC}	Thermal Resistance Junction-Case	---	1.3	°C/W

P-Channel Electrical Characteristics ($T_J=25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-60	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10V, I_D=-30A$	---	10.5	13.5	$m\Omega$
		$V_{GS}=-4.5V, I_D=-30A$	---	13.5	17.5	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.0	-1.85	-2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-32V, V_{GS}=0V, T_J=25^{\circ}\text{C}$	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
Q_g	Total Gate Charge	$V_{DS} = -30V, V_{GS} = -10V,$ $I_D = -17A$	---	121	---	nC
Q_{gs}	Gate-Source Charge		---	20	---	
Q_{gd}	Gate-Drain Charge		---	32	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD} = -30V, R_L = 30\Omega$ $I_D = -1A, V_{GEN} = -10V, R_g = 6$	---	20	---	ns
T_r	Rise Time		---	20	---	
$T_{d(off)}$	Turn-Off Delay Time		---	205	---	
T_f	Fall Time		---	90	---	
C_{iss}	Input Capacitance	$V_{DS}=-30V, V_{GS}=0V, f=1.0\text{MHz}$	---	5600	---	pF
C_{oss}	Output Capacitance		---	510	---	
C_{rss}	Reverse Transfer Capacitance		---	480	---	

Diode Characteristics

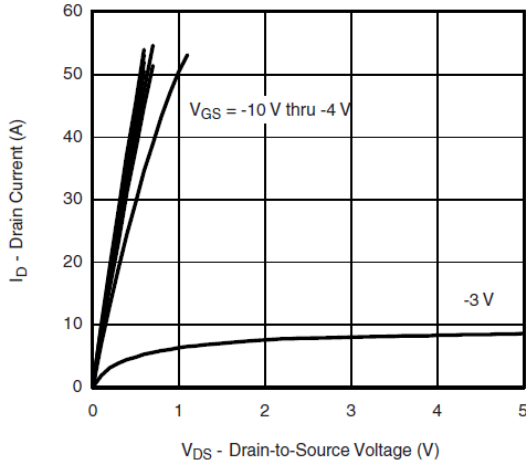
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$T_C=25\text{ }^{\circ}\text{C}$	---	---	-64	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V, I_S=-1A, T_J=25^{\circ}\text{C}$	---	---	-1.2	V

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The value in any given application depends on the user's specific board design.

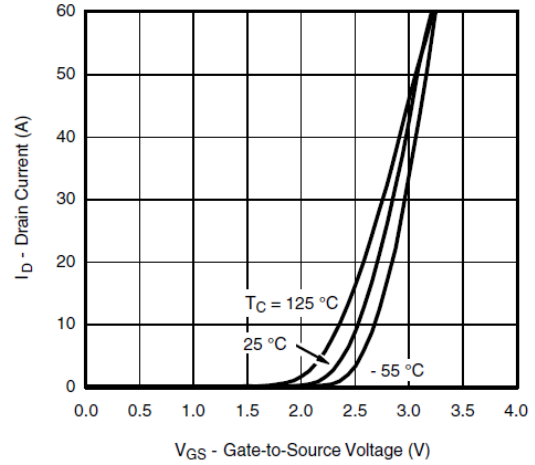
B: Repetitive rating, pulse width limited by junction temperature.

C: The current rating is based on the $t_s \leq 10s$ junction to ambient thermal resistance rating.

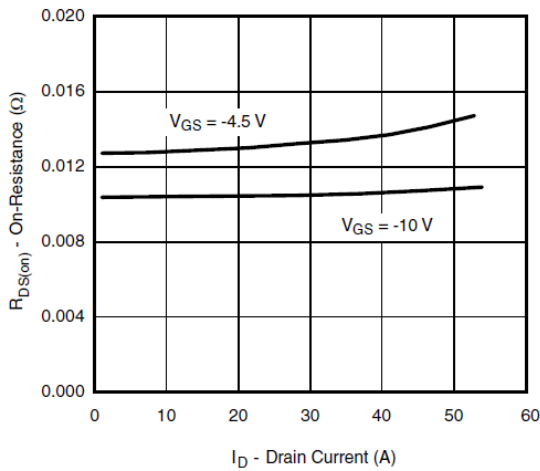
P-Channel Typical Characteristics



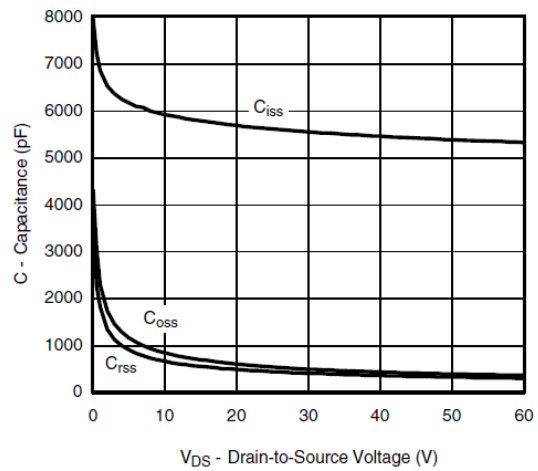
Output Characteristics



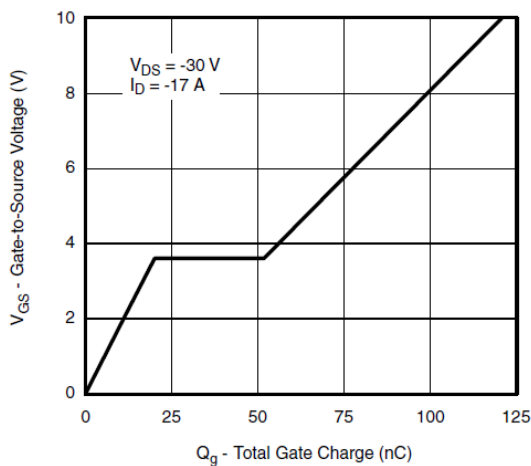
Transfer Characteristics



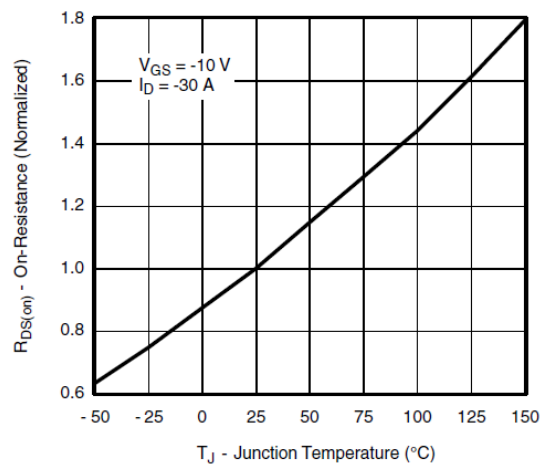
On-Resistance vs. Drain Current



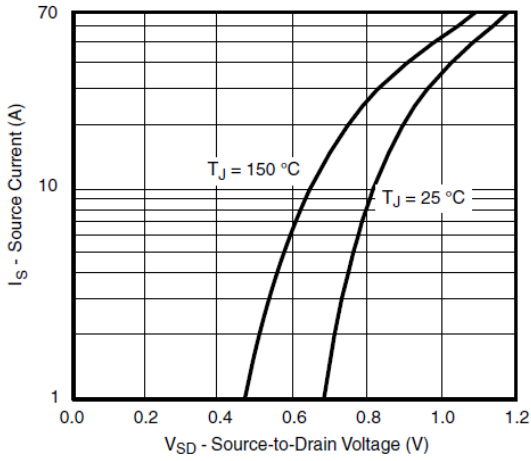
Capacitance



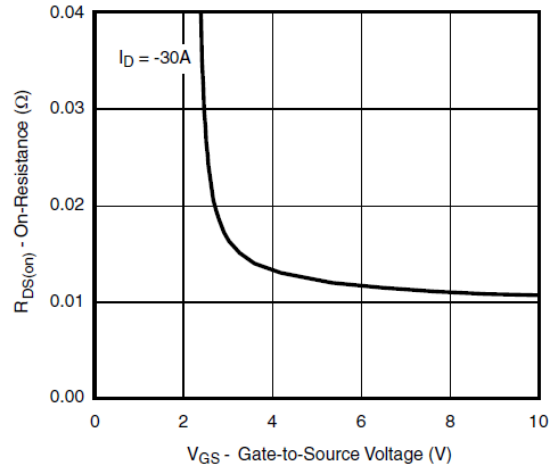
Gate Charge



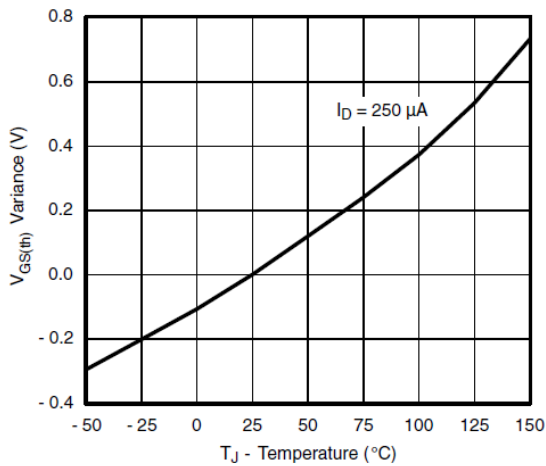
On-Resistance vs. Junction Temperature



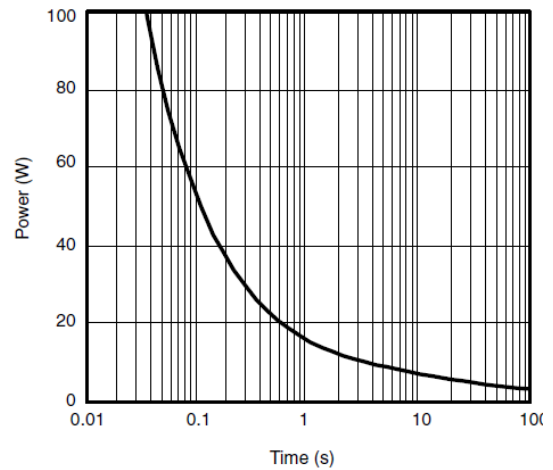
Source-Drain Diode Forward Voltage



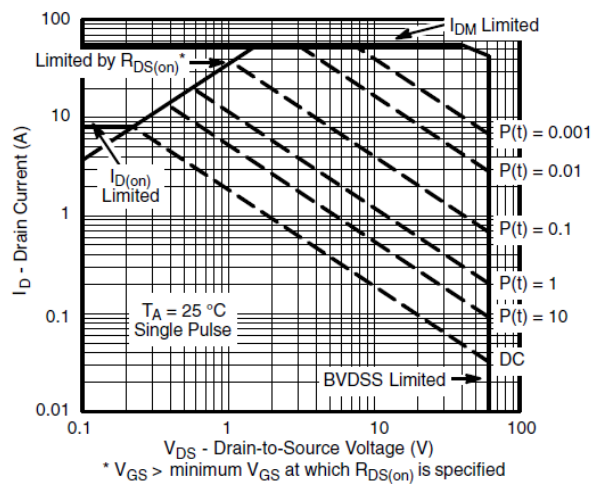
On-Resistance vs. Gate-to-Source Voltage



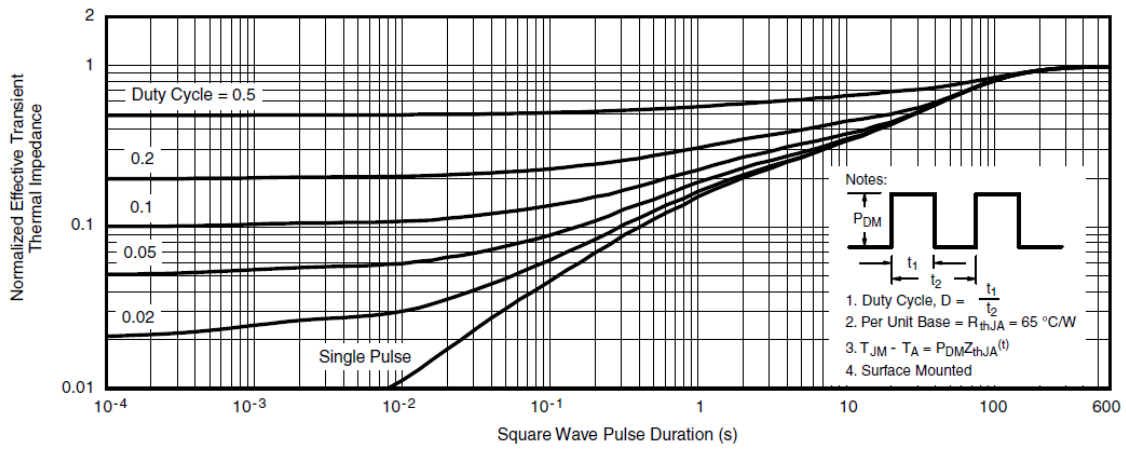
Threshold Voltage



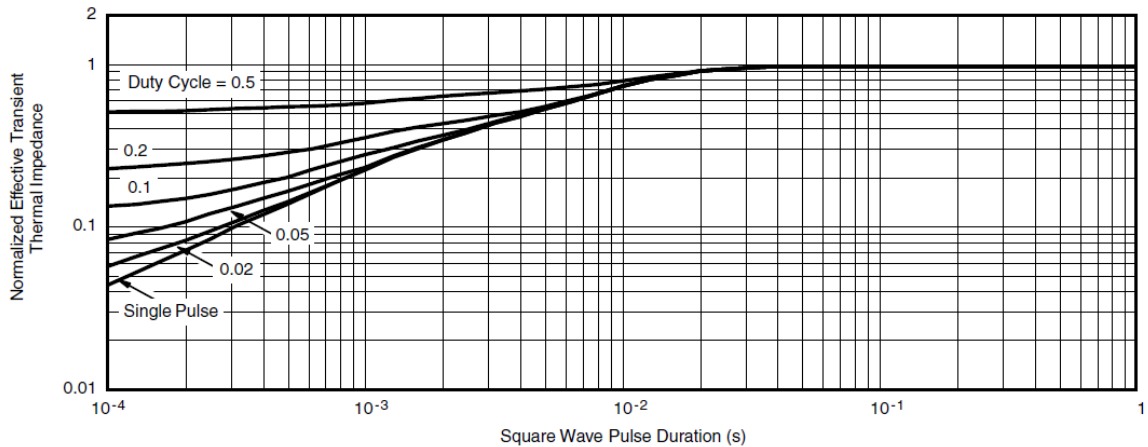
Single Pulse Power, Junction-to-Ambient



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case



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